



# PSMN2R5-40YLD

40 V logic level MOSFET

8 July 2019

Preliminary data sheet

## 1. General description

Logic level gate drive N-channel enhancement mode MOSFET.

## 2. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <a href="#">Fig. 2</a>	[1]	-	-	120	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <a href="#">Fig. 1</a>		-	-	147	W
T <sub>j</sub>	junction temperature			-55	-	175	°C
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>		-	2.2	2.5	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>		-	2.7	3.3	mΩ
Dynamic characteristics							
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 4.5 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>		-	5.9	11.8	nC
Q <sub>G(tot)</sub>	total gate charge			-	25	35	nC

[1] 120A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 3. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	<p>LFPAK56; Power-SO8 (SOT669)</p>	<p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 4. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R5-40YLD	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669

## 5. Limiting values

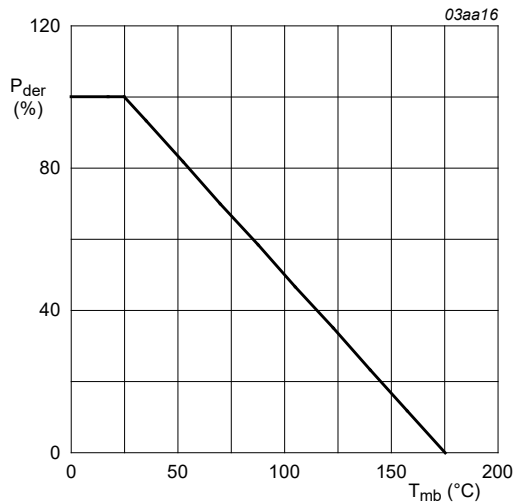
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ }^{\circ}\text{C} \leq T_j \leq 175\text{ }^{\circ}\text{C}$		-	40	V
$V_{DSM}$	peak drain-source voltage	$t_p \leq 20\text{ ns}$ ; $f \leq 500\text{ kHz}$ ; $E_{DS(AL)} \leq 200\text{ nJ}$ ; pulsed		-	45	V
$V_{DGR}$	drain-gate voltage	$25\text{ }^{\circ}\text{C} \leq T_j \leq 175\text{ }^{\circ}\text{C}$ ; $R_{GS} = 20\text{ k}\Omega$		-	40	V
$V_{GS}$	gate-source voltage			-20	20	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$ ; Fig. 1		-	147	W
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; Fig. 2	[1]	-	120	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ }^{\circ}\text{C}$ ; Fig. 2		-	120	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ }^{\circ}\text{C}$ ; Fig. 3		-	701	A
$T_{stg}$	storage temperature			-55	175	$^{\circ}\text{C}$
$T_j$	junction temperature			-55	175	$^{\circ}\text{C}$
$T_{sld(M)}$	peak soldering temperature			-	260	$^{\circ}\text{C}$
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25\text{ }^{\circ}\text{C}$		-	120	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ }^{\circ}\text{C}$		-	701	A
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 48\text{ A}$ ; $V_{sup} \leq 40\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; unclamped; $t_p = 172\text{ }\mu\text{s}$	[2]	-	215	mJ
		$I_D = 25\text{ A}$ ; $V_{sup} \leq 40\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; unclamped; $t_p = 695\text{ }\mu\text{s}$	[2]	-	452	mJ
$I_{AS}$	non-repetitive avalanche current	$V_{sup} = 40\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $R_{GS} = 50\text{ }\Omega$	[2]	-	120	A

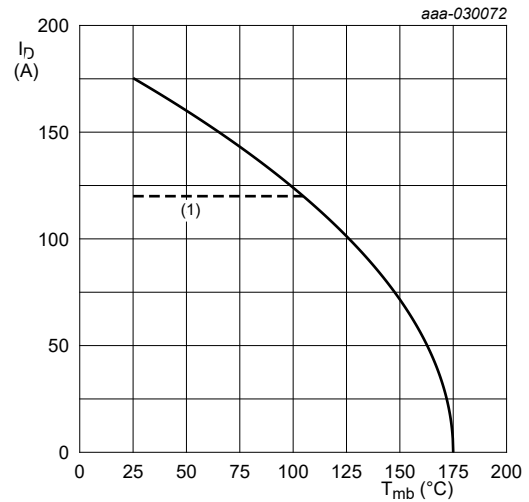
[1] 120A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] Protected by 100% test



$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

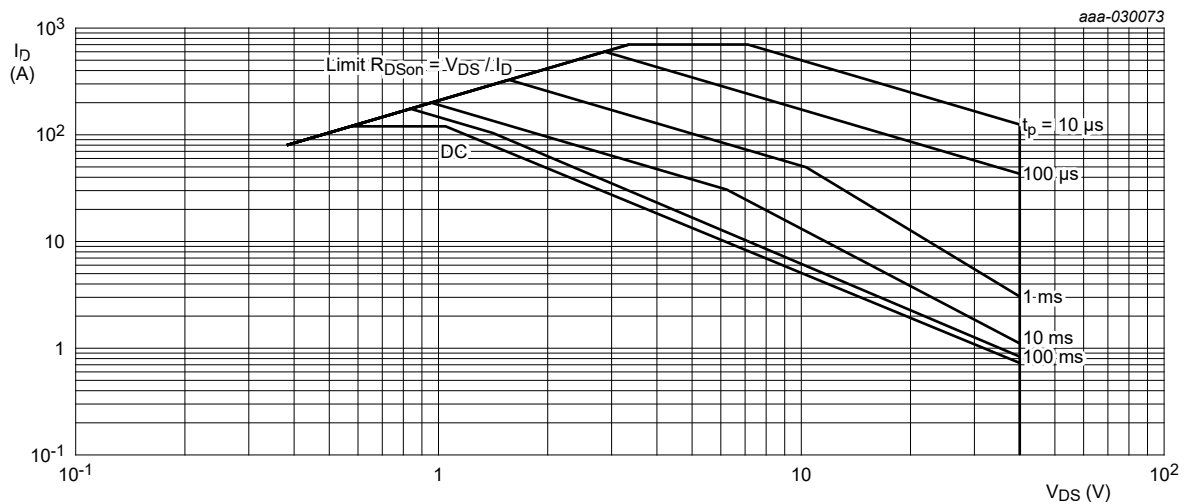
**Fig. 1.** Normalized total power dissipation as a function of mounting base temperature



$V_{GS} \geq 10\text{ V}$

(1) 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

**Fig. 2.** Continuous drain current as a function of mounting base temperature



$T_{mb} = 25^\circ\text{C}$ ;  $I_{DM}$  is a single pulse

**Fig. 3.** Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 6. Thermal characteristics

**Table 5.** Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 4</a>	-	0.92	1.02	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	<a href="#">Fig. 5</a>	-	42	-	K/W
		<a href="#">Fig. 6</a>	-	85	-	K/W

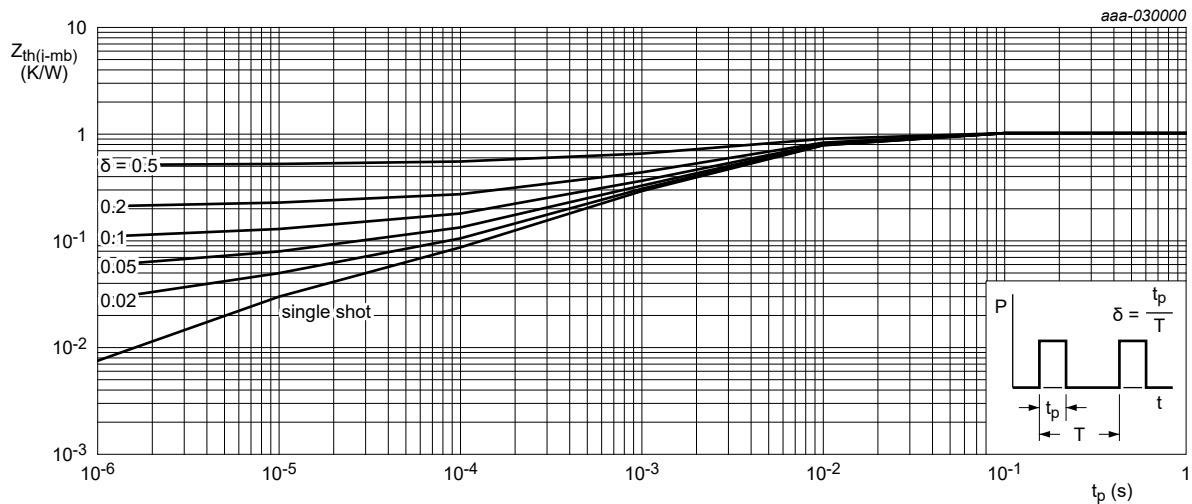
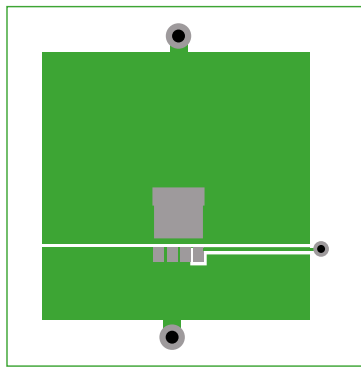
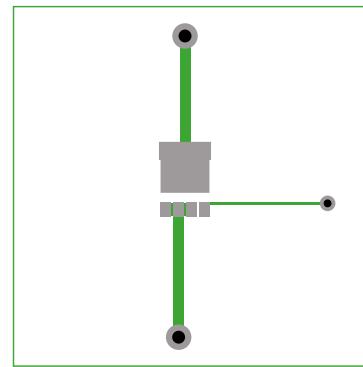


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration



Copper area 25.4 mm square; 70  $\mu$ m thick on FR4 board

Fig. 5. PCB layout for thermal resistance from junction to ambient



70  $\mu$ m thick copper on FR4 board

Fig. 6. PCB layout with minimum footprint for thermal resistance from junction to ambient

## 7. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = 25 ^\circ C$	40	-	-	V
		$I_D = 250 \mu A$ ; $V_{GS} = 0 V$ ; $T_j = -55 ^\circ C$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 mA$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 ^\circ C$	1.35	1.75	2.05	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 ^\circ C \leq T_j \leq 150 ^\circ C$	-	-4.3	-	mV/K
$I_{DSS}$	drain leakage current	$V_{DS} = 32 V$ ; $V_{GS} = 0 V$ ; $T_j = 25 ^\circ C$	-	0.01	1	$\mu A$
		$V_{DS} = 32 V$ ; $V_{GS} = 0 V$ ; $T_j = 125 ^\circ C$	-	[tbd]	-	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 16 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	2	100	nA
		$V_{GS} = -16 V$ ; $V_{DS} = 0 V$ ; $T_j = 25 ^\circ C$	-	2	100	nA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>		-	2.2	2.5	m $\Omega$
		$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 175\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>		-	-	4.9	m $\Omega$
		$V_{GS} = 4.5\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>		-	2.7	3.3	m $\Omega$
		$V_{GS} = 4.5\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 175\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>		-	-	6.4	m $\Omega$
$R_G$	gate resistance	$f = 1\text{ MHz}$ ; $T_j = 25\text{ }^\circ\text{C}$		0.3	0.7	1.8	$\Omega$
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 25\text{ A}$ ; $V_{DS} = 20\text{ V}$ ; $V_{GS} = 4.5\text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>		-	25	35	nC
		$I_D = 25\text{ A}$ ; $V_{DS} = 20\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>		-	56	78	nC
		$I_D = 0\text{ A}$ ; $V_{DS} = 0\text{ V}$ ; $V_{GS} = 10\text{ V}$		-	31	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25\text{ A}$ ; $V_{DS} = 20\text{ V}$ ; $V_{GS} = 4.5\text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>		-	10	15	nC
$Q_{GS(th)}$	pre-threshold gate-source charge			-	6	9	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge			-	4.1	6.2	nC
$Q_{GD}$	gate-drain charge			-	5.9	11.8	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25\text{ A}$ ; $V_{DS} = 20\text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>		-	2.8	-	V
$C_{iss}$	input capacitance	$V_{DS} = 20\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $f = 1\text{ MHz}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 14</a>		-	3988	5583	pF
$C_{oss}$	output capacitance			-	941	1317	pF
$C_{rss}$	reverse transfer capacitance			-	141	310	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 20\text{ V}$ ; $R_L = 0.8\text{ }\Omega$ ; $V_{GS} = 4.5\text{ V}$ ; $R_{G(ext)} = 5\text{ }\Omega$		-	9	-	ns
$t_r$	rise time			-	6.7	-	ns
$t_{d(off)}$	turn-off delay time			-	50	-	ns
$t_f$	fall time			-	15	-	ns
$Q_{oss}$	output charge	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; $f = 1\text{ MHz}$ ; $T_j = 25\text{ }^\circ\text{C}$		-	30	-	nC
<b>Source-drain diode</b>							
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 15</a>		-	0.8	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; <a href="#">Fig. 16</a>		-	31	-	ns
$Q_r$	recovered charge		[1]	-	25	-	nC
$t_a$	reverse recovery rise time			-	17	-	ns
$t_b$	reverse recovery fall time			-	14	-	ns

[1] includes capacitive recovery

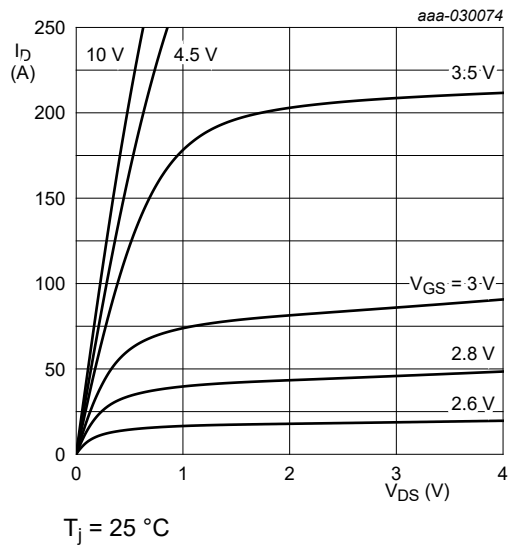


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

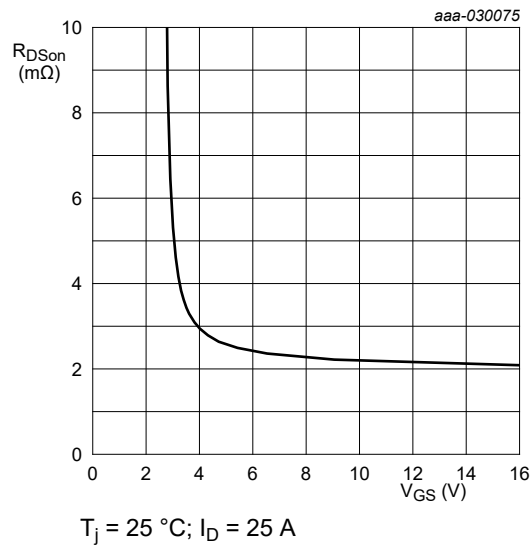


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

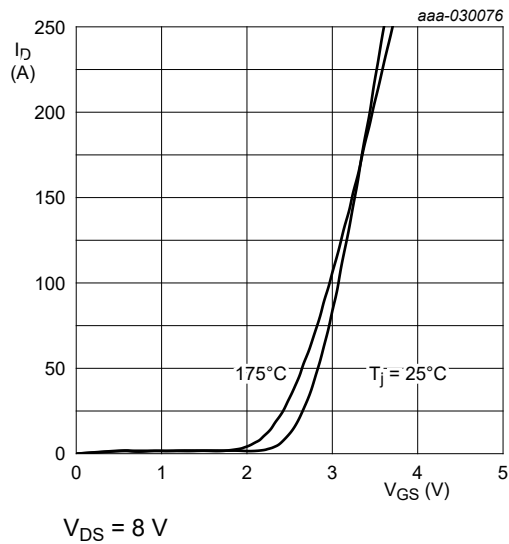


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

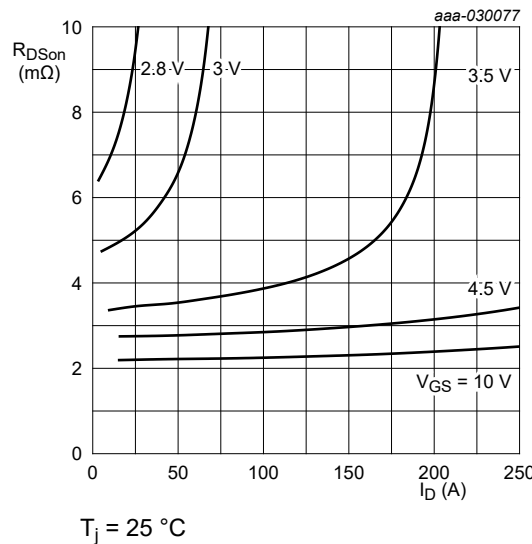


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

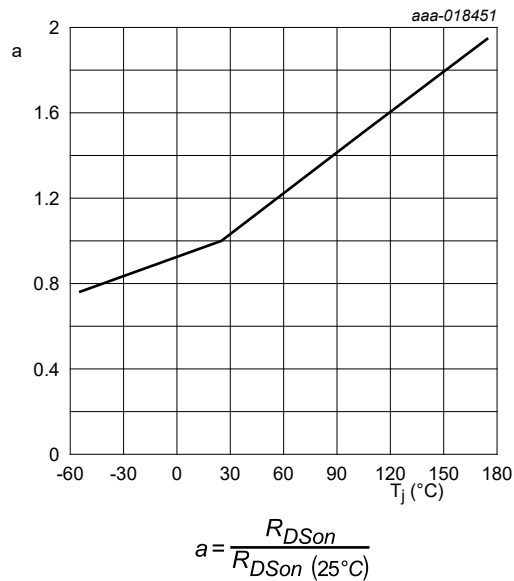


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

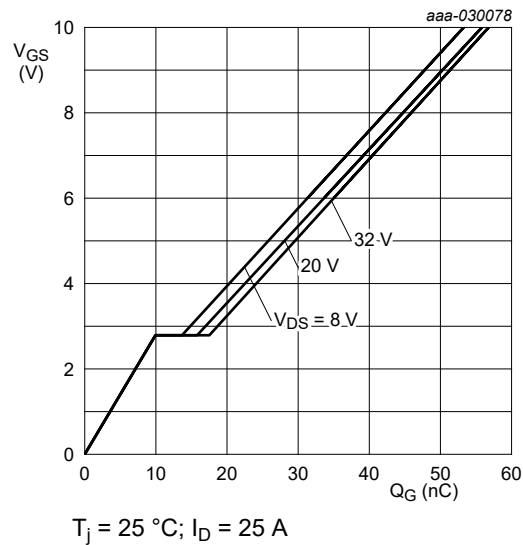


Fig. 12. Gate-source voltage as a function of gate charge; typical values

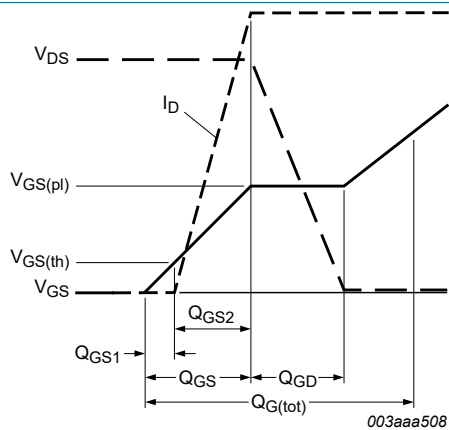


Fig. 13. Gate charge waveform definitions

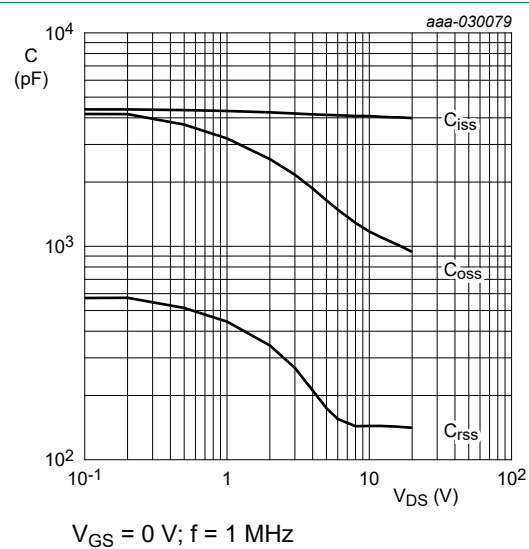
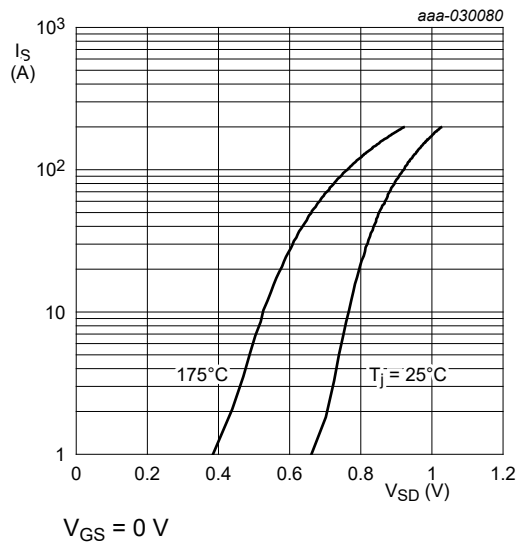
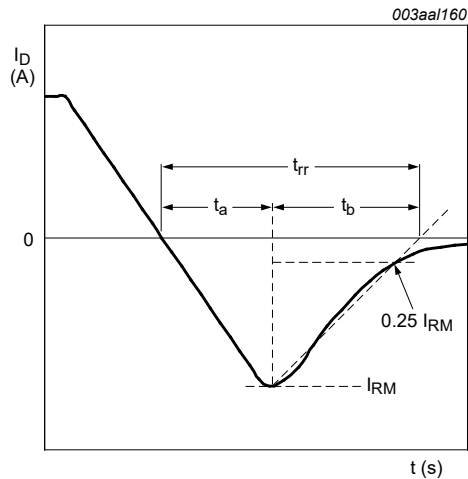


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



**Fig. 15.** Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values



**Fig. 16.** Reverse recovery timing definition



8. Package outline

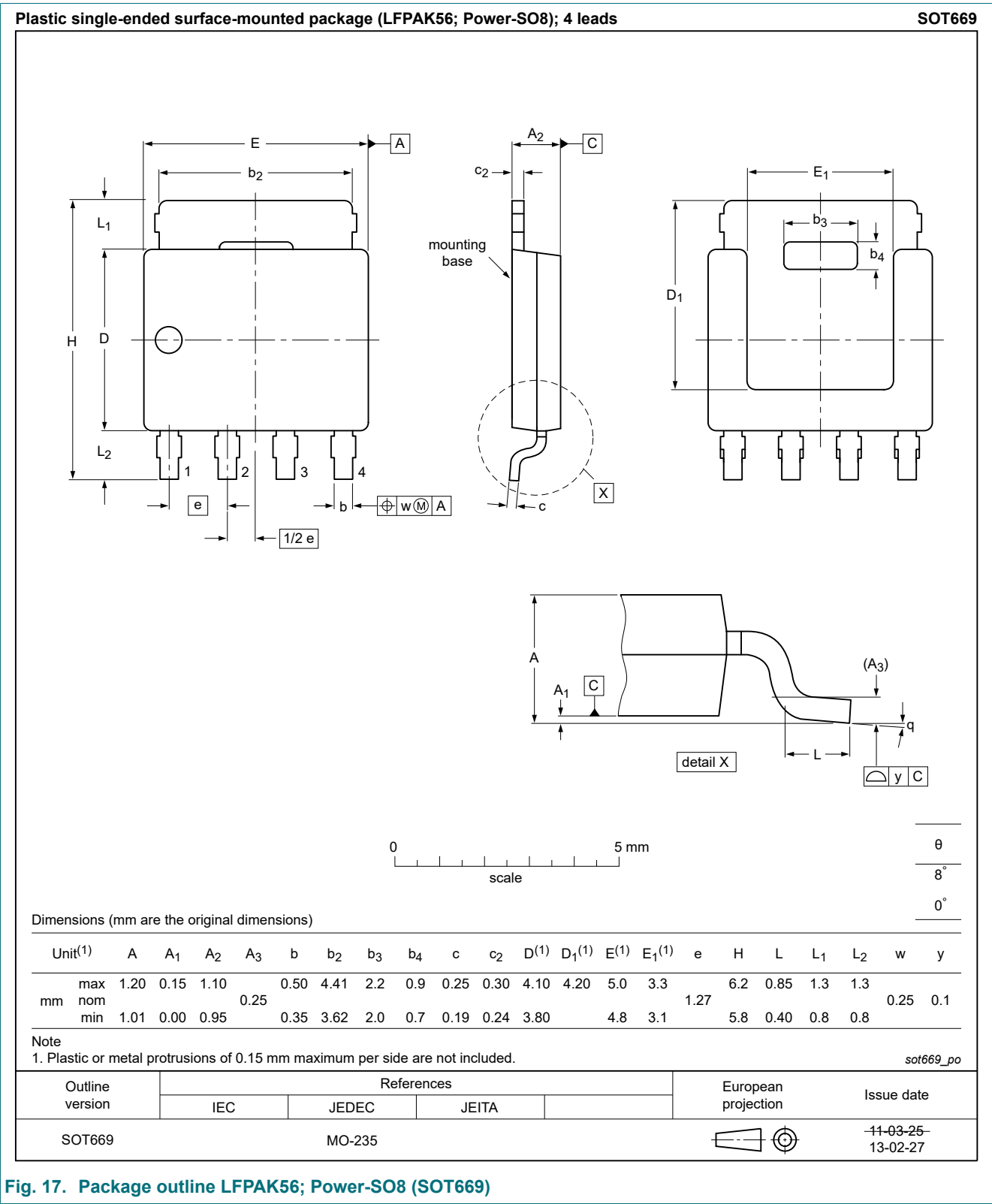


Fig. 17. Package outline LPAK56; Power-SO8 (SOT669)

9. Soldering

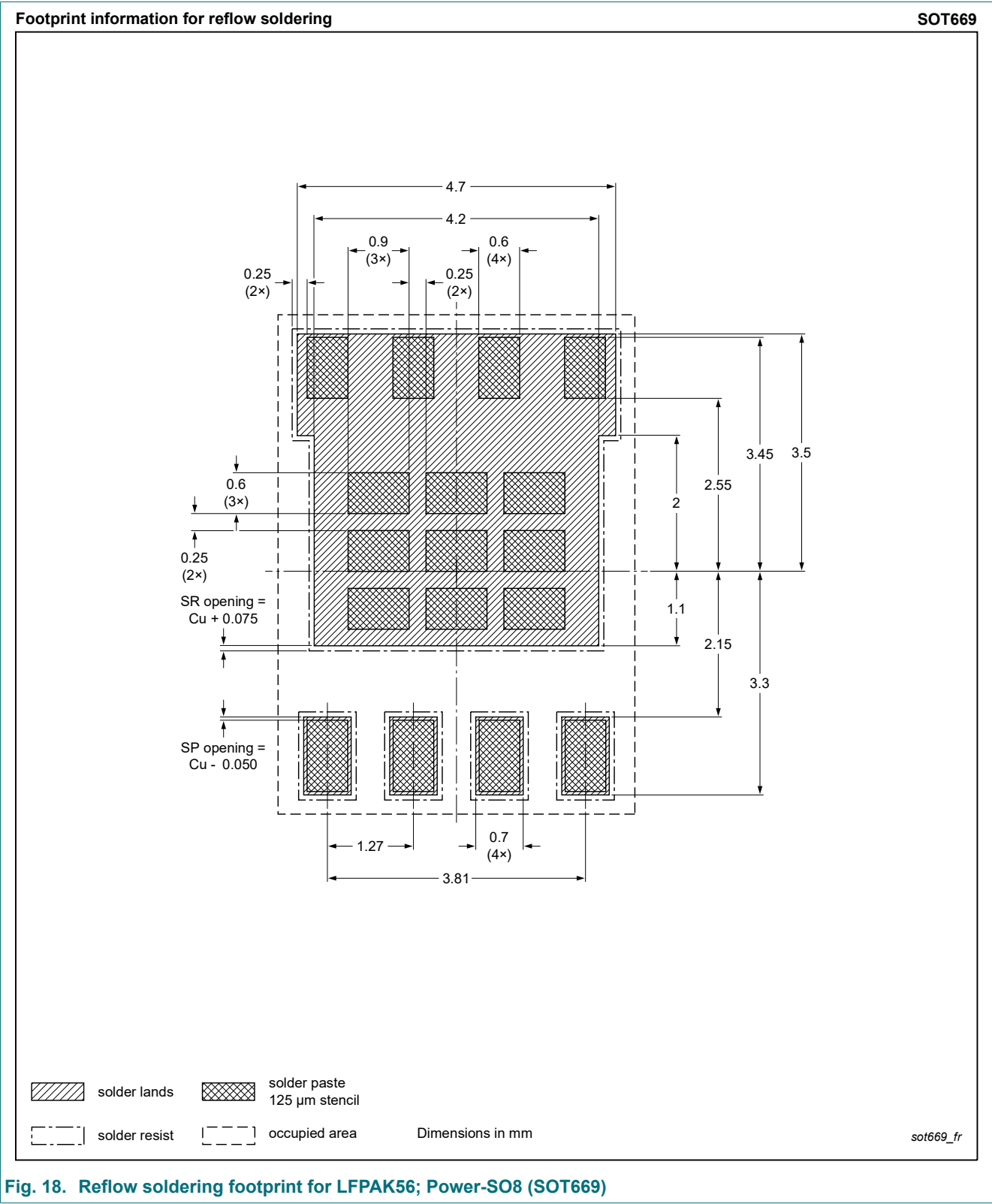


Fig. 18. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)

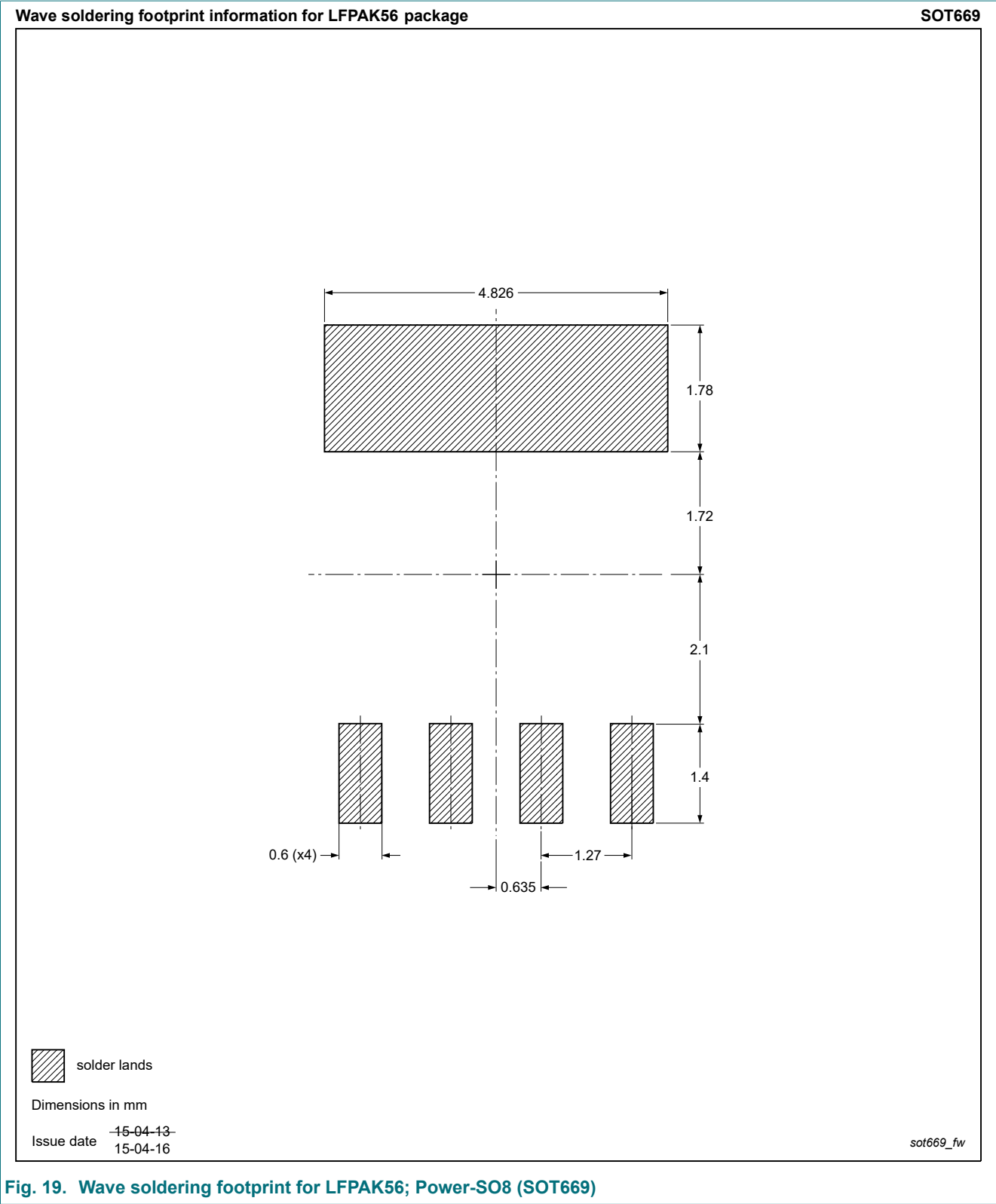


Fig. 19. Wave soldering footprint for LFPAK56; Power-SO8 (SOT669)

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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